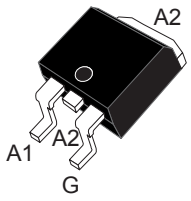
T810T-8G

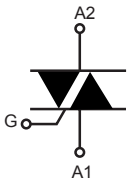
Datasheet

8 A - 800 V logic level T-series Triac in D²PAK



D²PAK

A2: Anode2
A1: Anode1
G: Gate



Features

- 150 °C maximum junction temperature
- Three quadrants
- High commutation on resistive loads
- Surge capability V_{DSM}, V_{RSM} = 900 V
- Benefits:
  - Easy direct control by MCU thanks to low 10 mA I_{GT}
  - Increase of thermal margin due to extended working T_j up to 150 °C

Applications

- General purpose AC line load switching
- Small home appliances with resistive loads
- Hybrid relays
- Inrush current limiting circuits
- Overvoltage crowbar protection

Description

The SMD T810T-8G Triac can be used for the on/off or phase angle control function in general purpose AC switching with resistive loads. A Logic level T-series Triac, the T810T-8G can be controlled directly from an MCU with a simplified circuit.

T-series triacs are optimized for high EMI constraints. The surface mount D²PAK package enables compact SMT designs for automated manufacturing.

D²PAK's molding compound resin is halogen-free and meets UL94 flammability standard level V0.

Package environmentally friendly ECOPACK2 graded (RoHS and Halogen Free compliance).

Product status link
T810T-8G

Product summary	
$I_{T(RMS)}$	8 A
V_{DRM}/V_{RRM}	800 V
V_{DSM}/V_{RSM}	900 V
I_{GT}	10 mA

1 Characteristics

Table 1. Absolute maximum ratings (limiting values), T_j = 25 °C unless otherwise specified

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)		T_c = 131 °C	8	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25 °C)	t = 16.7 ms	T_j = 25 °C	63	A
		t = 20 ms		60	
I^2t	I^2t value for fusing	t_p = 10 ms	T_j = 25 °C	24	A^2s
dI/dt	Critical rate of rise of on-state current, I_G = 2 x I_{GT}, tr ≤ 100 ns	f = 50 Hz	T_j = 25 °C	100	A/µs
V_{DRM}/V_{RRM}	Repetitive peak off-state voltage		T_j = 125 °C	800	V
			T_j = 150 °C	600	V
V_{DSM}/V_{RSM}	Non Repetitive peak off-state voltage	t_p = 10 ms	T_j = 25 °C	900	V
I_{GM}	Peak gate current	t_p = 20 µs	T_j = 150 °C	4	A
V_{GM}	Peak Gate Voltage		T_j = 150 °C	5	V
$P_{G(AV)}$	Average gate power dissipation		T_j = 150 °C	1	W
T_{stg}	Storage junction temperature range			-40 to +150	°C
T_j	Operating junction temperature range			-40 to +150	°C

Table 2. Electrical characteristics (T_j = 25 °C, unless otherwise specified)

Symbol	Test conditions		Quadrants; T_j		Value	Unit
I_{GT} (1)	V_D = 12 V, R_L = 30 Ω		I - II - III	Min.	0.5	mA
			I - II - III	Max.	10	
V_{GT}	V_D = 12 V, R_L = 30 Ω		I - II - III	Max.	1.3	V
V_{GD}	V_D = 800 V, R_L = 3.3 kΩ	T_j = 125 °C	I - II - III	Min.	0.2	V
I_L	I_G = 1.2 x I_{GT}		I - III	Max.	20	mA
	I_G = 1.2 x I_{GT}		II	Max.	25	mA
I_H (2)	I_T = 500 mA, gate open			Max.	15	mA
dV/dt (2)	V_D = 536 V, gate open		T_j = 125 °C	Min.	250	V/µs
	V_D = 402 V, gate open		T_j = 150 °C	Min.	170	V/µs
(dI/dt)c (2)	(dV/dt)c = 0.1 V/µs		T_j = 125 °C	Min.	6	A/ms
			T_j = 150 °C		4.2	
	(dV/dt)c = 10 V/µs		T_j = 125 °C	Min.	3.2	A/ms
			T_j = 150 °C		1.4	

1. *Minimum I_{GT} is guaranteed at 5% of I_{GT} max*
2. *For both polarities of A2 referenced to A1.*

Table 3. Static characteristics

Symbol	Test conditions	T_j		Value	Unit
V_{TM} (1)	I_T = 11.3 A, t_p = 380 µs	25 °C	Max.	1.55	V
V_{TO}(1)	Threshold on-state voltage	150 °C	Max.	0.85	V
R_D(1)	Dynamic resistance	150 °C	Max.	57	mΩ
I_{DRM}/I_{RRM}	V_{DRM} = V_{RRM} = 800 V	25 °C	Max.	5	µA
		125°C		0.8	mA
	V_{DRM} = V_{RRM} = 600 V	150 °C	Max.	2.4	mA

1. *For both polarities of A2 referenced to A1.*

Table 4. Thermal resistance

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	Max.	1.9	°C/W
$R_{th(j-a)}$	Junction to ambient (AC) for S_{Cu} = 2 cm²	Typ.	45	

1.1 Characteristics (curves)

Figure 1. Maximum power dissipation versus on-state RMS current

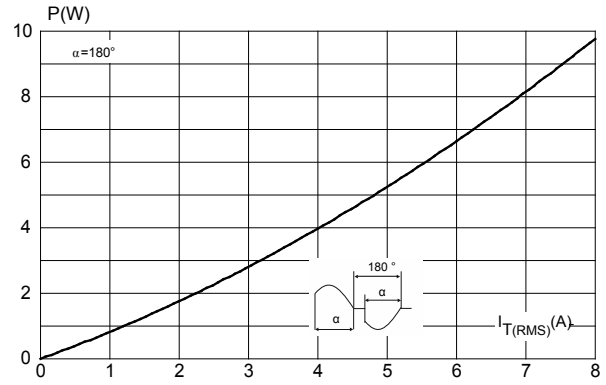


Figure 2. On-state RMS current versus case temperature

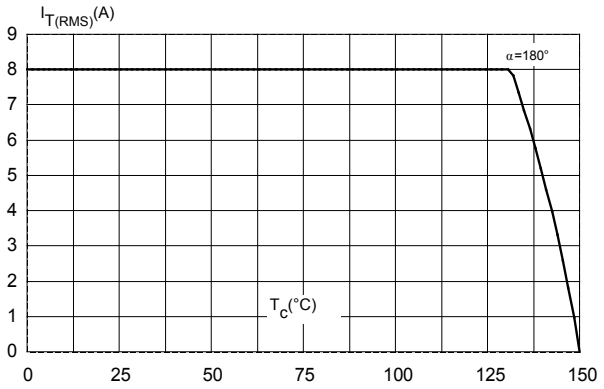


Figure 3. On-state RMS current versus ambient temperature (free air convection)

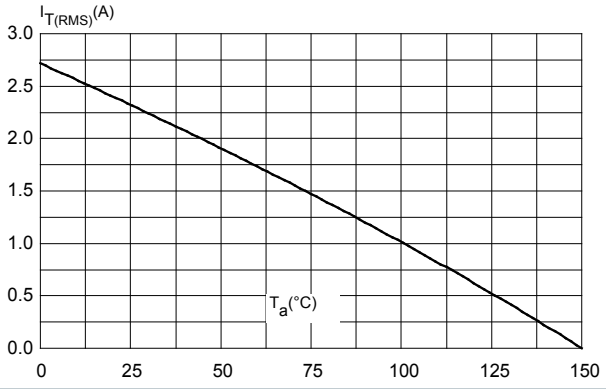


Figure 4. Relative variation of thermal impedance versus pulse duration

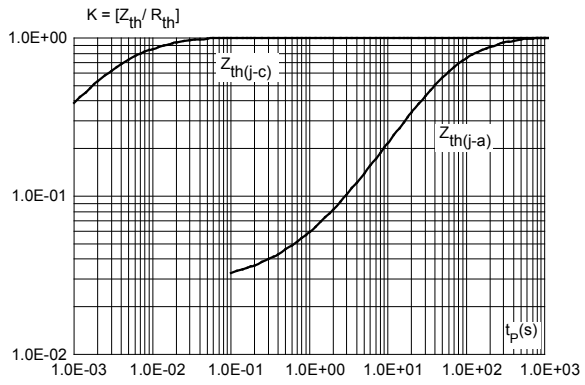


Figure 5. On-state characteristics (maximum values)

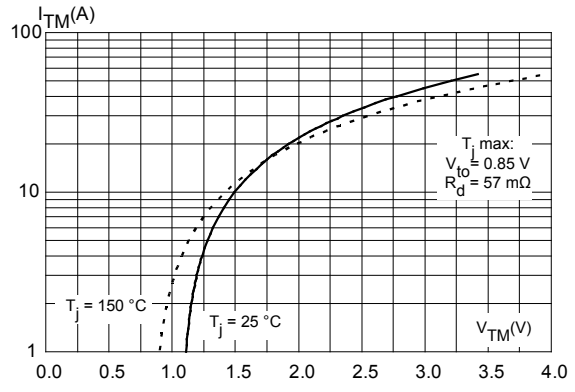


Figure 6. Surge peak on-state current versus number of cycles

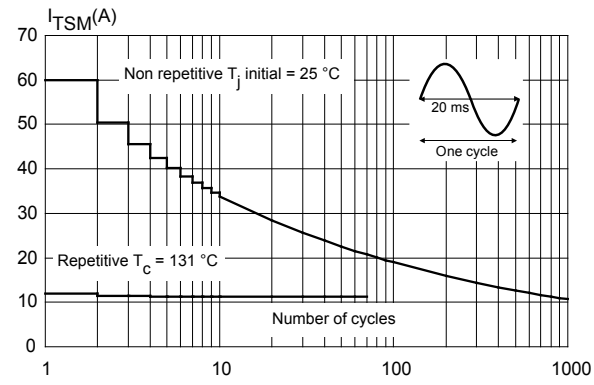


Figure 7. Non repetitive surge peak on-state current

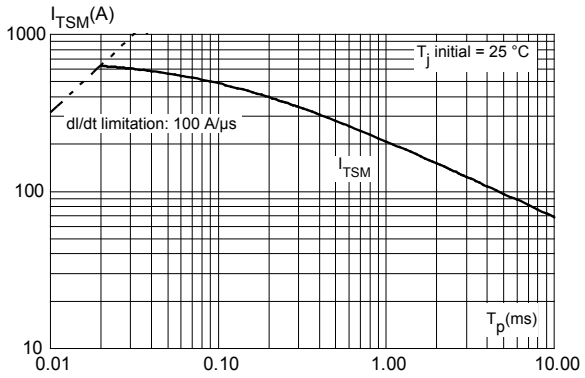


Figure 8. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

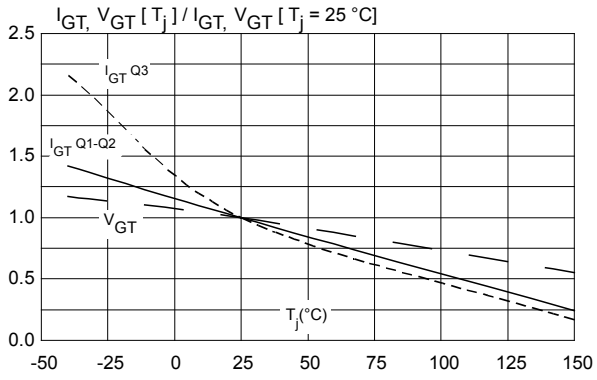


Figure 9. Relative variation of critical rate of decrease of main current versus junction temperature (typical values)

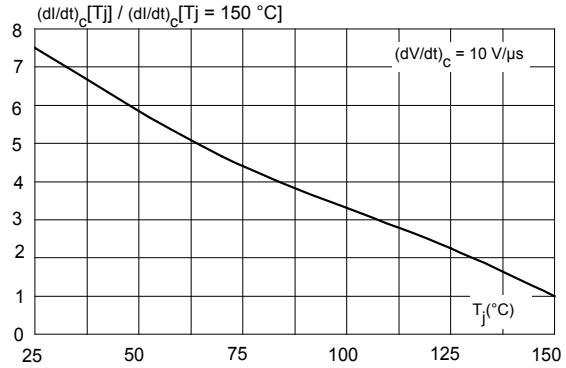


Figure 10. Relative variation of holding current and latching current versus junction temperature (typical values)

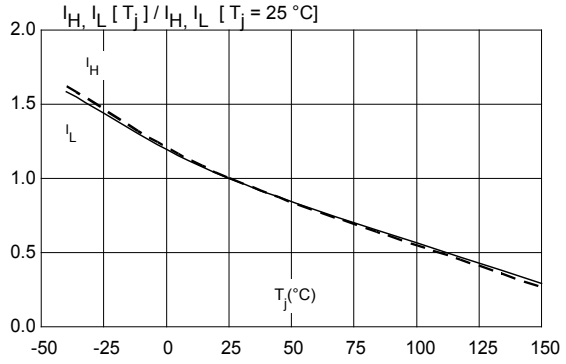


Figure 11. Relative variation of critical rate of decrease of main current (dI/dt)C versus reapplied $(dI/dt)_C$ (maximum values)

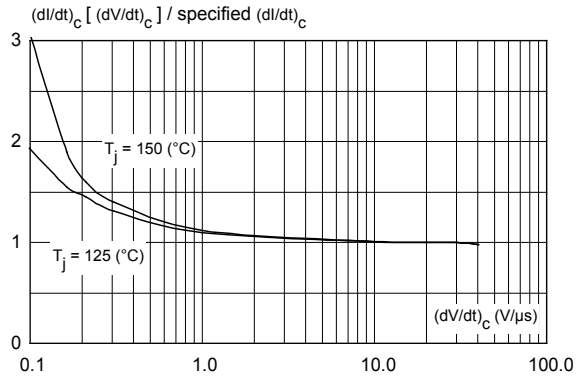


Figure 12. Relative variation of static dV/dt immunity versus junction temperature (typical values)

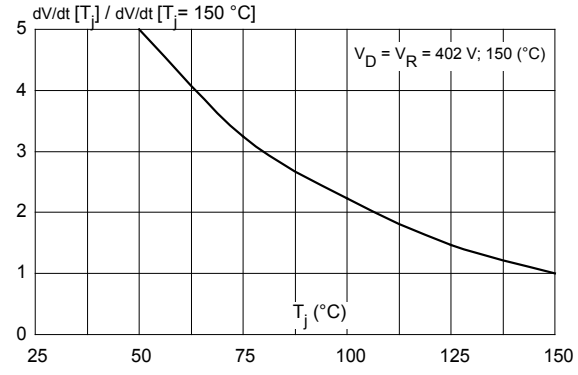


Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)

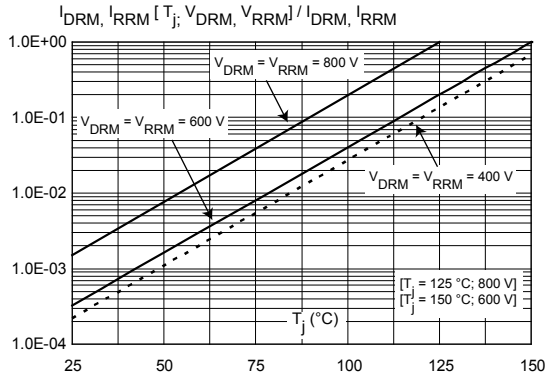
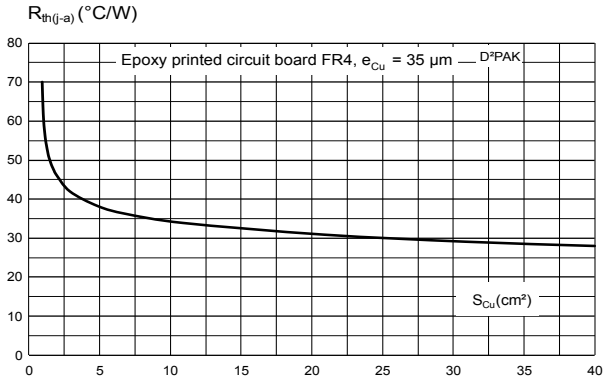


Figure 14. Thermal resistance junction to ambient versus copper surface under tab



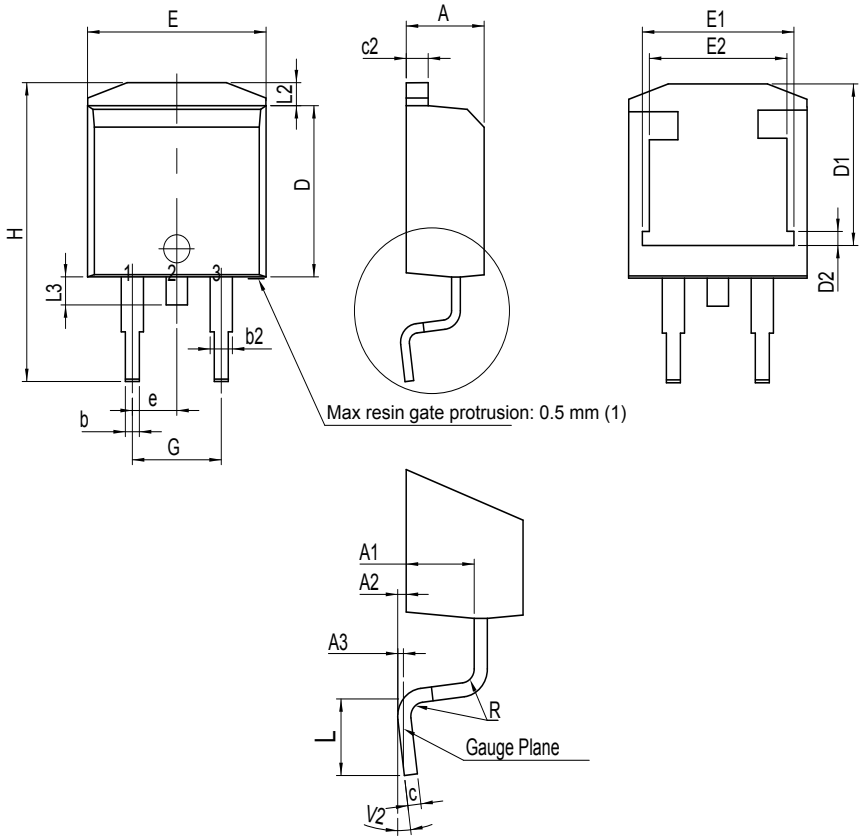
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 D²PAK package information

- ECOPACK2 compliant
- Lead-free package leads finishing
- Molding compound resin is halogen-free and meets UL standard level V0

Figure 15. D²PAK package outline



(1) Resin gate is accepted in each of position shown on the drawing, or their symmetrical.

Table 5. D²PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.1693		0.1811
A1	2.49		2.69	0.0980		0.1059
A2	0.03		0.23	0.0012		0.0091
A3		0.25			0.0098	
b	0.70		0.93	0.0276		0.0366
b2	1.25		1.7	0.0492		0.0669
c	0.45		0.60	0.0177		0.0236
c2	1.21		1.36	0.0476		0.0535
D	8.95		9.35	0.3524		0.3681
D1	7.50		8.00	0.2953		0.3150
D2	1.30		1.70	0.0512		0.0669
e		2.54			0.1	
E	10.00		10.28	0.3937		0.4047
E1	8.30		8.70	0.3268		0.3425
E2	6.85		7.25	0.2697		0.2854
G	4.88		5.28	0.1921		0.2079
H	15		15.85	0.5906		0.6240
L	1.78		2.28	0.0701		0.0898
L2	1.19		1.40	0.0468		0.0551
L3	1.40		1.75	0.0551		0.0689
R		0.40			0.0157	
V2[2]	0°		8°	0°		8°

1. *Dimensions in inches are given for reference only*
2. *Degrees*

Figure 16. D²PAK recommended footprint (dimensions are in mm)

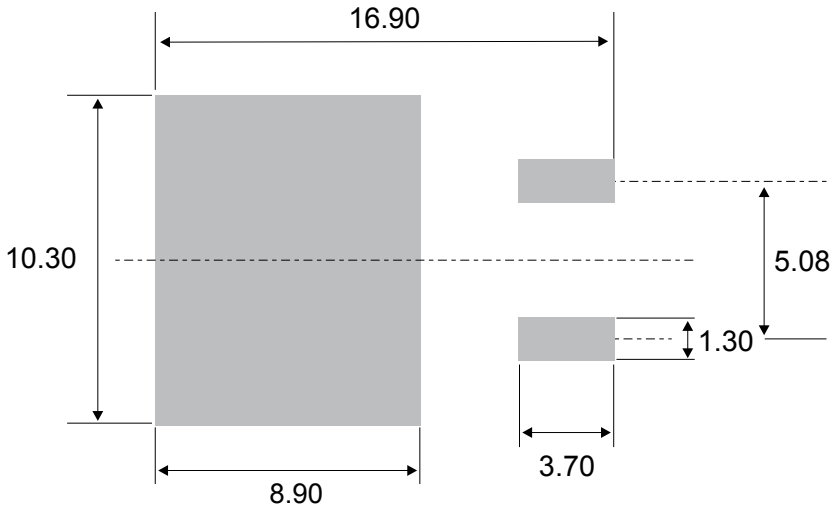
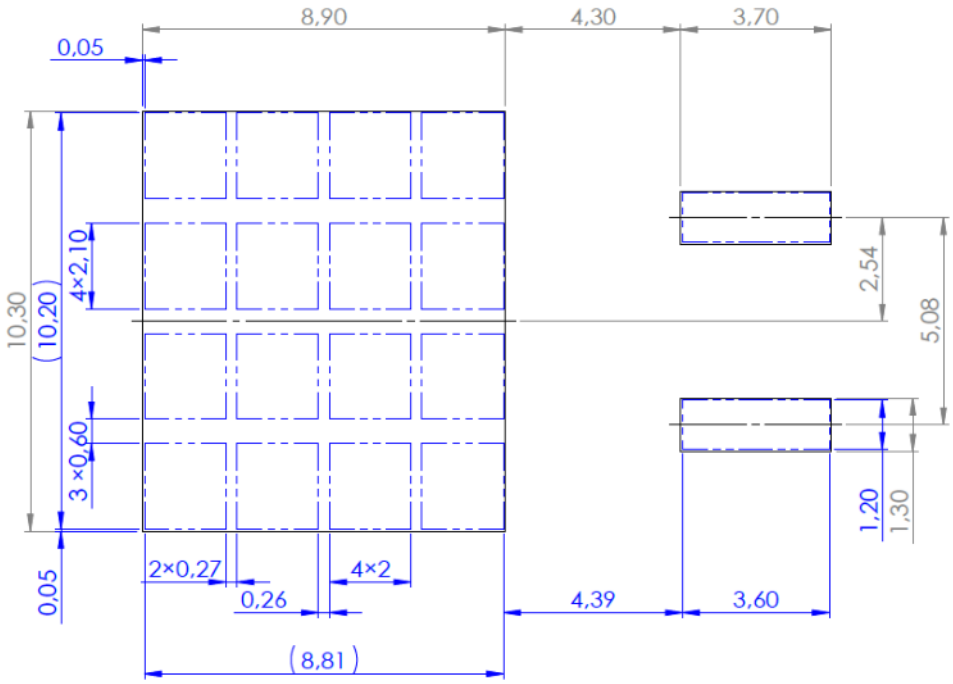


Figure 17. D²PAK stencil definitions(dimensions are in mm)



3 Ordering information

Figure 18. **Ordering information scheme**

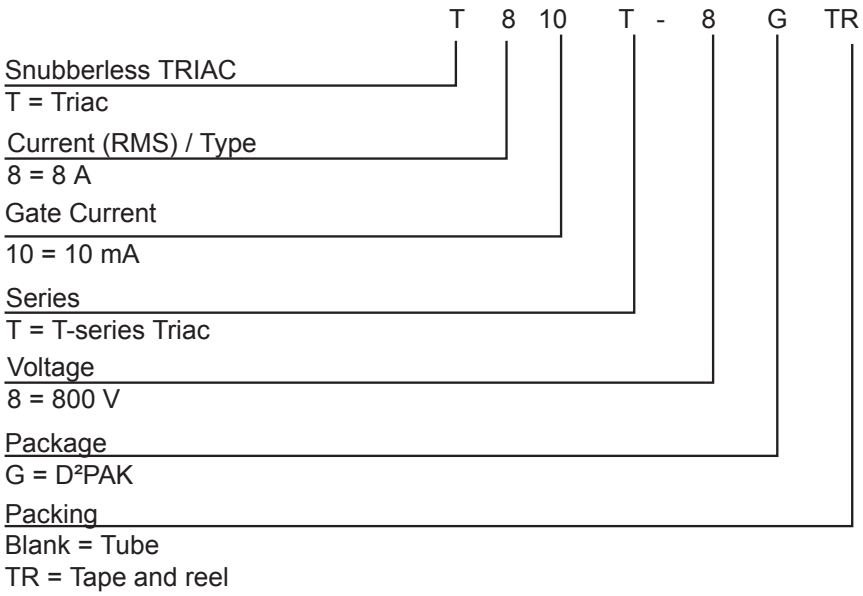


Table 6. **Ordering information**

Order code	Marking	Package	Weight	Base qty.	Delivery mode
T810T-8G-TR	T810T-8G	D²PAK	1.6 g	1000	Tape and reel
T810T-8G				50	Tube

Revision history

Table 7. **Document revision history**

Date	Version	Changes
04-Jun-2020	1	Initial release.
20-Oct-2020	2	Updated Table 5.

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